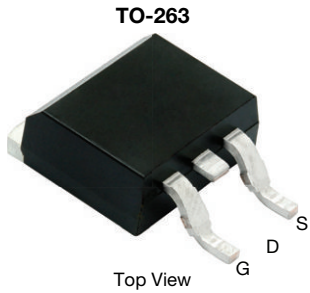


## N-Channel 150 V (D-S) MOSFET

PRODUCT SUMMARY			
V <sub>DS</sub> (V)	R <sub>DS(on)</sub> (Ω) MAX.	I <sub>D</sub> (A)	Q <sub>g</sub> (TYP.)
150	0.0075 at V <sub>GS</sub> = 10 V	128	63 nC
	0.0084 at V <sub>GS</sub> = 7.5 V	119	



### FEATURES

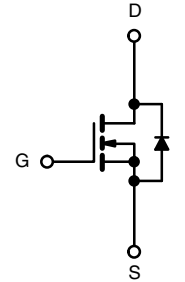
- ThunderFET® power MOSFET
- Maximum 175 °C junction temperature
- 100 % R<sub>g</sub> and UIS tested
- Material categorization:



**RoHS**  
COMPLIANT  
HALOGEN  
**FREE**

### APPLICATIONS

- Power supplies:
  - Uninterruptible power supplies
  - AC/DC switch-mode power supplies
  - Lighting
- Synchronous rectification
- DC/DC converter
- Motor drive switch
- DC/AC inverter
- Solar micro inverter
- Class D audio amplifier
- Battery management



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T <sub>C</sub> = 25 °C, unless otherwise noted)				
PARAMETER		SYMBOL	LIMIT	UNIT
Drain-Source Voltage		V <sub>DS</sub>	150	V
Gate-Source Voltage		V <sub>GS</sub>	± 20	
Continuous Drain Current (T <sub>J</sub> = 150 °C)	T <sub>C</sub> = 25 °C	I <sub>D</sub>	128	A
	T <sub>C</sub> = 125 °C		74	
Pulsed Drain Current (t = 100 μs)		I <sub>DM</sub>	240	
Avalanche Current	L = 0.1 mH	I <sub>AS</sub>	60	
Single Avalanche Energy <sup>a</sup>		E <sub>AS</sub>	180	mJ
Maximum Power Dissipation <sup>a</sup>	T <sub>C</sub> = 25 °C	P <sub>D</sub>	375 <sup>b</sup>	W
	T <sub>C</sub> = 125 °C		125 <sup>b</sup>	
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	-55 to +175	°C

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-Ambient (PCB Mount) <sup>c</sup>		R <sub>thJA</sub>	40	°C/W
Junction-to-Case (Drain)		R <sub>thJC</sub>	0.4	

### Notes

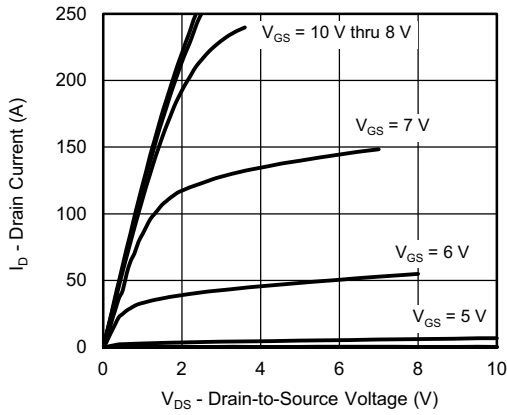
- Duty cycle ≤ 1 %.
- See SOA curve for voltage derating.
- When mounted on 1" square PCB (FR4 material).

<b>SPECIFICATIONS</b> ( $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise noted)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
<b>Static</b>						
Drain-Source Breakdown Voltage	$V_{DS}$	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	150	-	-	V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	2	-	5	
Gate-Body Leakage	$I_{GSS}$	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$	-	-	$\pm 250$	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 150\text{ V}, V_{GS} = 0\text{ V}$	-	-	1	$\mu\text{A}$
		$V_{DS} = 150\text{ V}, V_{GS} = 0\text{ V}, T_J = 125\text{ }^\circ\text{C}$	-	-	100	
		$V_{DS} = 150\text{ V}, V_{GS} = 0\text{ V}, T_J = 175\text{ }^\circ\text{C}$	-	-	2	mA
On-State Drain Current <sup>a</sup>	$I_{D(on)}$	$V_{DS} \geq 10\text{ V}, V_{GS} = 10\text{ V}$	90	-	-	A
Drain-Source On-State Resistance <sup>a</sup>	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 30\text{ A}$	-	0.0075	-	$\Omega$
		$V_{GS} = 7.5\text{ V}, I_D = 30\text{ A}$	-	0.0084	-	
Forward Transconductance <sup>a</sup>	$g_{fs}$	$V_{DS} = 15\text{ V}, I_D = 30\text{ A}$	-	52	-	S
<b>Dynamic <sup>b</sup></b>						
Input Capacitance	$C_{ISS}$	$V_{GS} = 0\text{ V}, V_{DS} = 75\text{ V}, f = 1\text{ MHz}$	-	3425	-	pF
Output Capacitance	$C_{OSS}$		-	535	-	
Reverse Transfer Capacitance	$C_{RSS}$		-	26	-	
Total Gate Charge <sup>c</sup>	$Q_g$	$V_{DS} = 75\text{ V}, V_{GS} = 10\text{ V}, I_D = 60\text{ A}$	-	63	95	nC
Gate-Source Charge <sup>c</sup>	$Q_{gs}$		-	19.5	-	
Gate-Drain Charge <sup>c</sup>	$Q_{gd}$		-	20.5	-	
Gate Resistance	$R_g$	$f = 1\text{ MHz}$	1.5	3	5	$\Omega$
Turn-On Delay Time <sup>c</sup>	$t_{d(on)}$	$V_{DD} = 75\text{ V}, R_L = 1.25\text{ }\Omega$ $I_D \cong 60\text{ A}, V_{GEN} = 10\text{ V}, R_g = 1\text{ }\Omega$	-	15	30	ns
Rise Time <sup>c</sup>	$t_r$		-	114	220	
Turn-Off Delay Time <sup>c</sup>	$t_{d(off)}$		-	28	56	
Fall Time <sup>c</sup>	$t_f$		-	8	16	
<b>Drain-Source Body Diode Ratings and Characteristics <sup>b</sup></b> ( $T_C = 25\text{ }^\circ\text{C}$ )						
Pulsed Current ( $t = 100\text{ }\mu\text{s}$ )	$I_{SM}$		-	-	240	A
Forward Voltage <sup>a</sup>	$V_{SD}$	$I_F = 30\text{ A}, V_{GS} = 0\text{ V}$	-	0.73	1.2	V
Reverse Recovery Time	$t_{rr}$	$I_F = 30\text{ A}, di/dt = 100\text{ A}/\mu\text{s}$	-	110	220	ns
Peak Reverse Recovery Charge	$I_{RM(REC)}$		-	10	20	A
Reverse Recovery Charge	$Q_{rr}$		-	0.5	1	$\mu\text{C}$

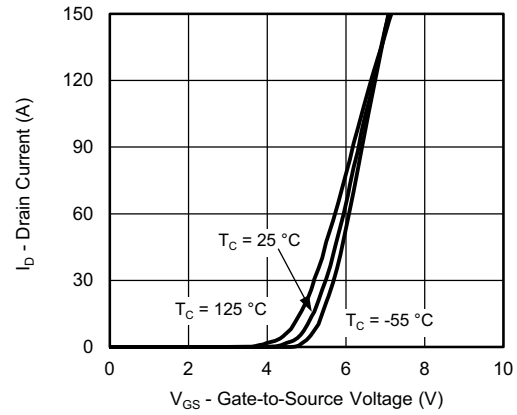
**Notes**

- a. Pulse test; pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$ .  
 b. Guaranteed by design, not subject to production testing.  
 c. Independent of operating temperature.

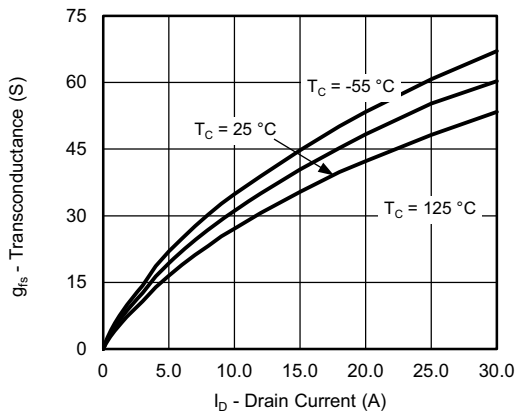
## TYPICAL CHARACTERISTICS ( $T_A = 25\text{ }^\circ\text{C}$ , unless otherwise noted)



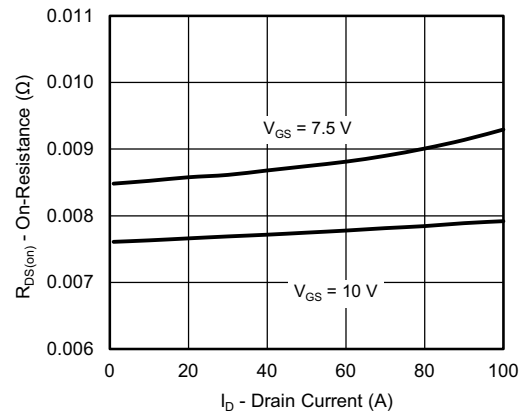
Output Characteristics



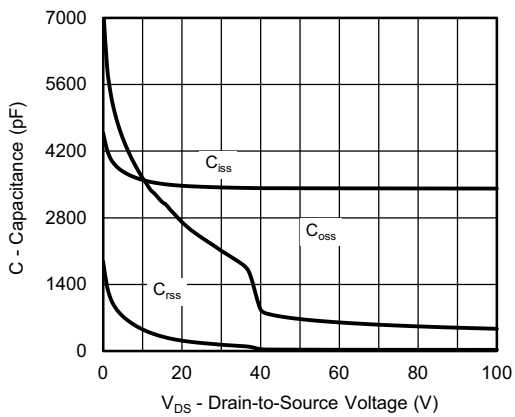
Transfer Characteristics



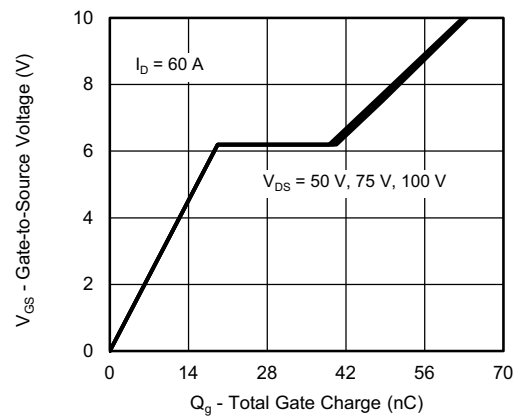
Transconductance



On-Resistance vs. Drain Current

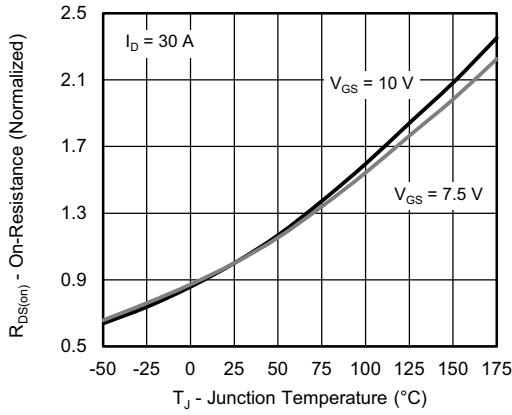


Capacitance

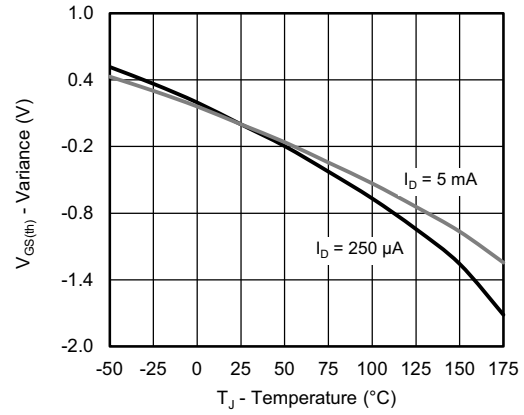


Gate Charge

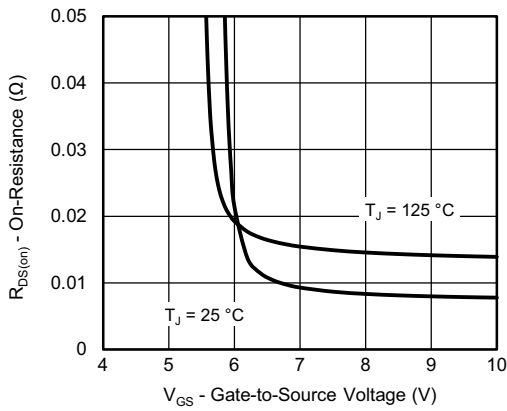
**TYPICAL CHARACTERISTICS** ( $T_A = 25\text{ }^\circ\text{C}$ , unless otherwise noted)



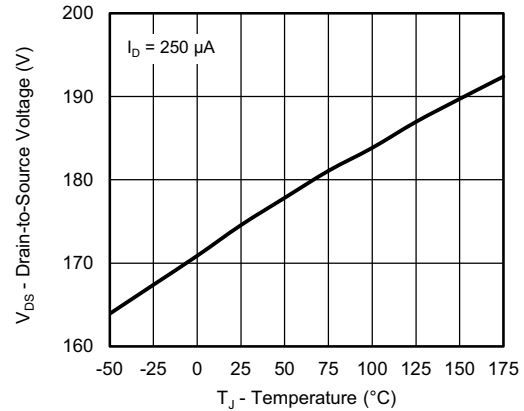
**On-Resistance vs. Junction Temperature**



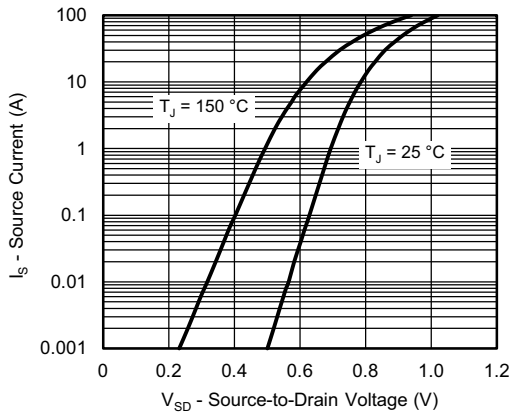
**Threshold Voltage**



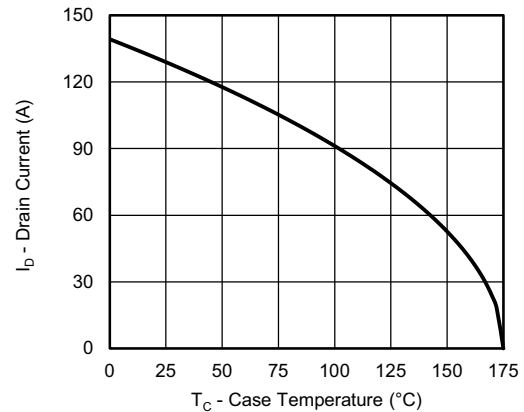
**On-Resistance vs. Gate-to-Source Voltage**



**Drain Source Breakdown vs. Junction Temperature**

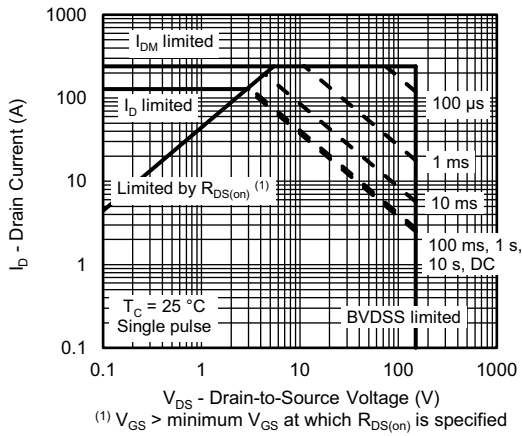


**Source Drain Diode Forward Voltage**

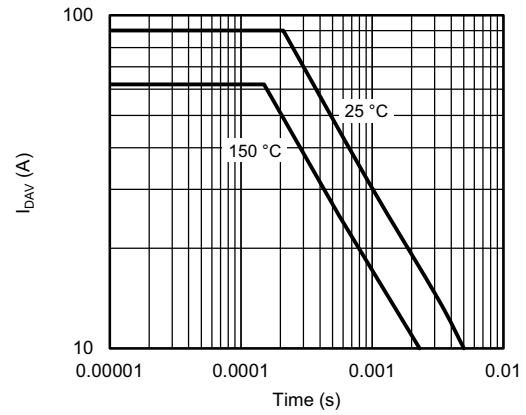


**Current De-Rating**

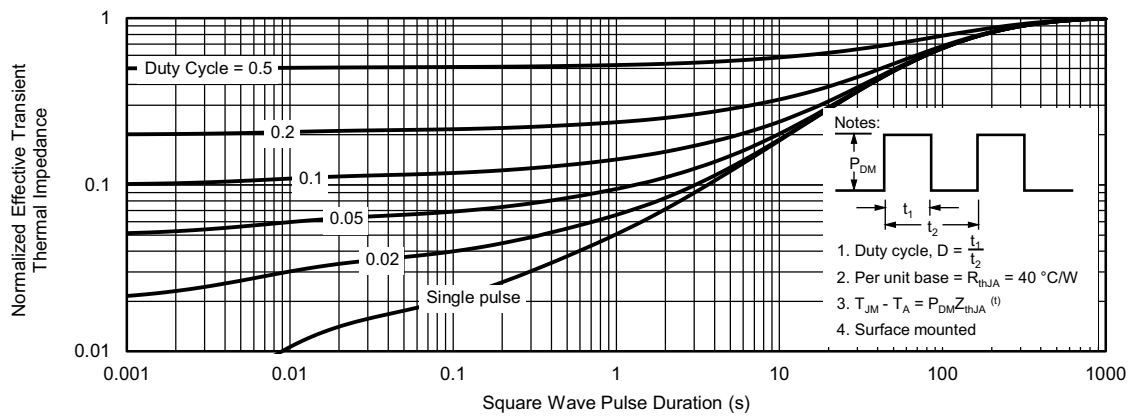
**THERMAL RATINGS** ( $T_A = 25\text{ }^\circ\text{C}$ , unless otherwise noted)



**Safe Operating Area**

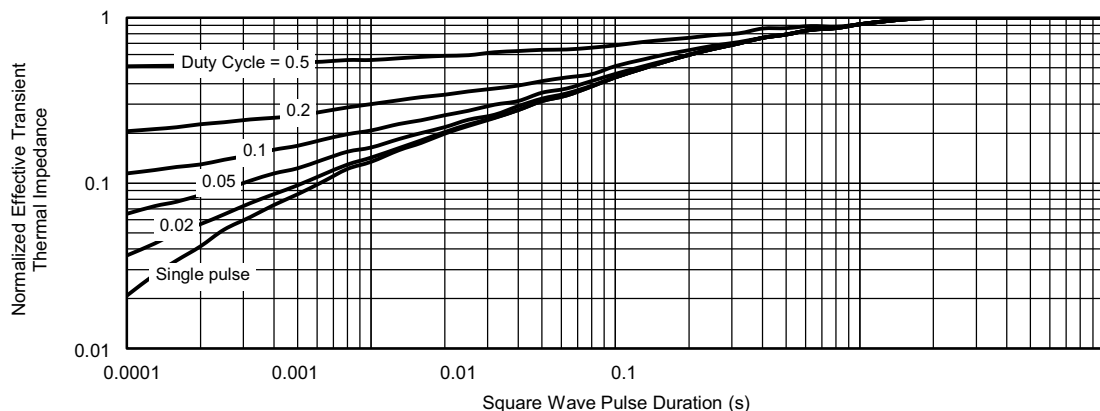


**$I_{DAV}$  vs. Time**



**Normalized Thermal Transient Impedance, Junction-to-Ambient**

**THERMAL RATINGS** ( $T_A = 25\text{ }^\circ\text{C}$ , unless otherwise noted)

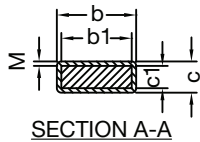


**Normalized Thermal Transient Impedance, Junction-to-Case**

**Note**


- The characteristics shown in the two graphs
  - Normalized Transient Thermal Impedance Junction to Ambient ( $25\text{ }^\circ\text{C}$ )
  - Normalized Transient Thermal Impedance Junction to Case ( $25\text{ }^\circ\text{C}$ )
 are given for general guidelines only to enable the user to get a “ball park” indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

### TO-263 (D<sup>2</sup>PAK): 3-LEAD

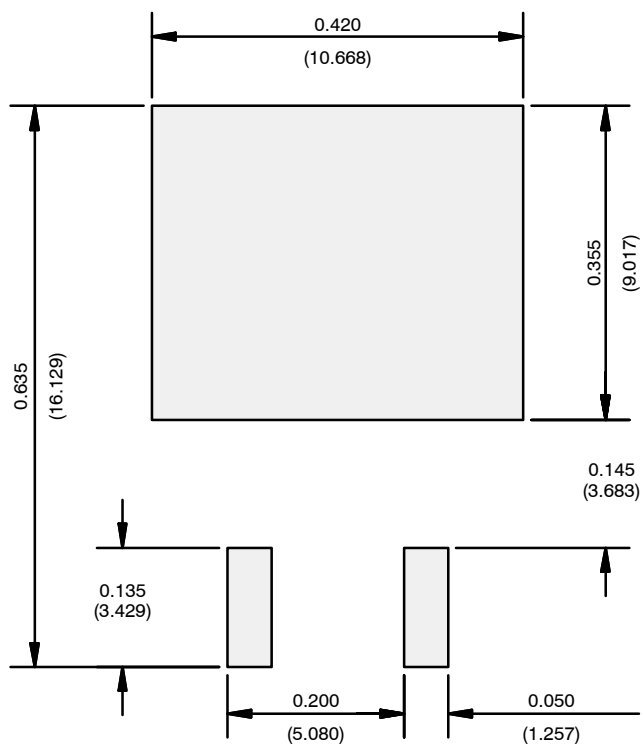


DIM.	INCHES		MILLIMETERS		
	MIN.	MAX.	MIN.	MAX.	
A	0.160	0.190	4.064	4.826	
b	0.020	0.039	0.508	0.990	
b1	0.020	0.035	0.508	0.889	
b2	0.045	0.055	1.143	1.397	
c*	Thin lead	0.013	0.018	0.330	0.457
	Thick lead	0.023	0.028	0.584	0.711
c1	Thin lead	0.013	0.017	0.330	0.431
	Thick lead	0.023	0.027	0.584	0.685
c2	0.045	0.055	1.143	1.397	
D	0.340	0.380	8.636	9.652	
D1	0.220	0.240	5.588	6.096	
D2	0.038	0.042	0.965	1.067	
D3	0.045	0.055	1.143	1.397	
D4	0.044	0.052	1.118	1.321	
E	0.380	0.410	9.652	10.414	
E1	0.245	-	6.223	-	
E2	0.355	0.375	9.017	9.525	
E3	0.072	0.078	1.829	1.981	
e	0.100 BSC		2.54 BSC		
K	0.045	0.055	1.143	1.397	
L	0.575	0.625	14.605	15.875	
L1	0.090	0.110	2.286	2.794	
L2	0.040	0.055	1.016	1.397	
L3	0.050	0.070	1.270	1.778	
L4	0.010 BSC		0.254 BSC		
M	-	0.002	-	0.050	
ECN: T13-0707-Rev. K, 30-Sep-13					
DWG: 5843					

**Notes**

- Plane B includes maximum features of heat sink tab and plastic.
- No more than 25 % of L1 can fall above seating plane by max. 8 mils.
- Pin-to-pin coplanarity max. 4 mils.
- \*: Thin lead is for SUB, SYB.  
Thick lead is for SUM, SYM, SQM.
- Use inches as the primary measurement.
-  This feature is for thick lead.

**RECOMMENDED MINIMUM PADS FOR D<sup>2</sup>PAK: 3-Lead**



Recommended Minimum Pads  
Dimensions in Inches/(mm)



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